

2SD2623

Silicon NPN epitaxial planar type

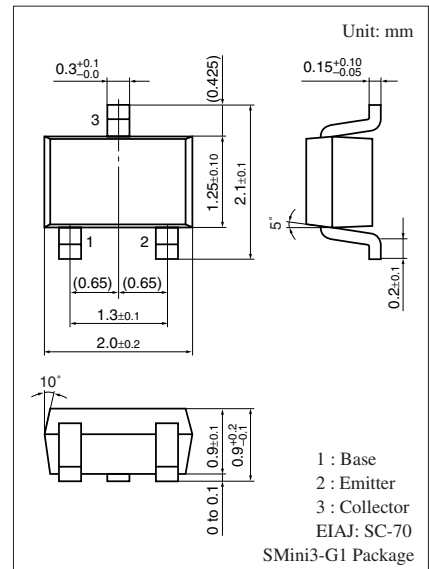
For low-frequency amplification

■ Features

- Low ON resistance R_{on}
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 25 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 20 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 12 | V |
| Collector current | I_C | 0.5 | A |
| Peak collector current | I_{CP} | 1 | A |
| Collector power dissipation | P_C | 150 | mW |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |



Marking Symbol: 2V

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|---------------|--|-----|------|------|----------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}$, $I_E = 0$ | 25 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 1 \text{ mA}$, $I_B = 0$ | 20 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu\text{A}$, $I_C = 0$ | 12 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 25 \text{ V}$, $I_E = 0$ | | | 100 | nA |
| Forward current transfer ratio *1,2 | h_{FE} | $V_{CE} = 2 \text{ V}$, $I_C = 0.5 \text{ A}$ | 200 | | 800 | — |
| Collector-emitter saturation voltage *1 | $V_{CE(sat)}$ | $I_C = 0.5 \text{ A}$, $I_B = 20 \text{ mA}$ | | 0.14 | 0.40 | V |
| Base-emitter saturation voltage *1 | $V_{BE(sat)}$ | $I_C = 0.5 \text{ A}$, $I_B = 50 \text{ mA}$ | | | 1.2 | V |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}$, $I_E = -50 \text{ mA}$, $f = 200 \text{ MHz}$ | | 200 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$ | | 10 | | pF |
| ON resistance *3 | R_{on} | | | 1.0 | | Ω |

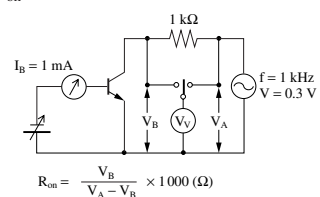
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

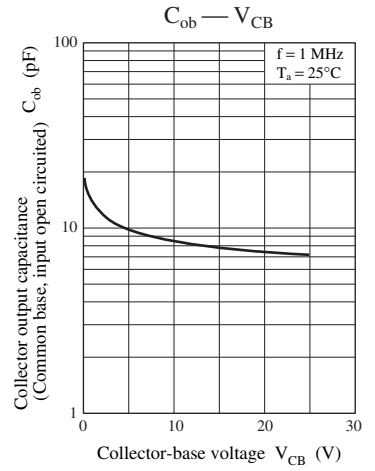
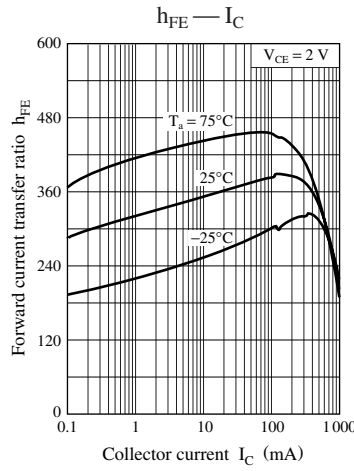
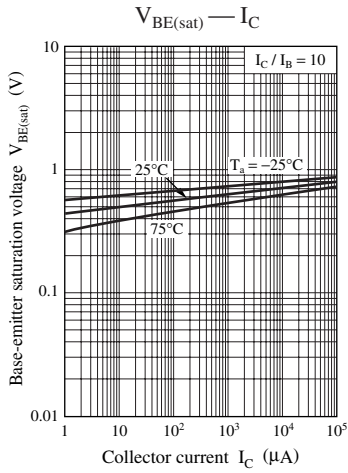
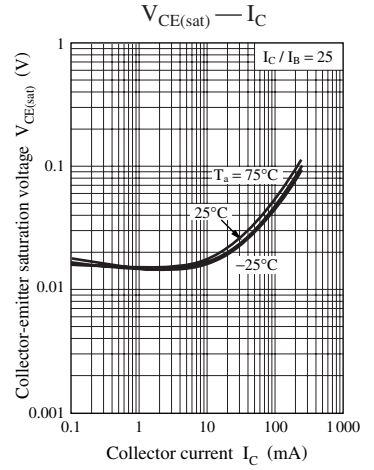
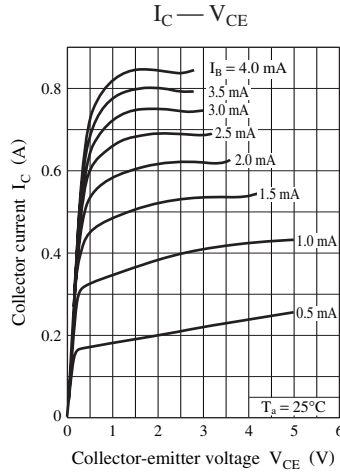
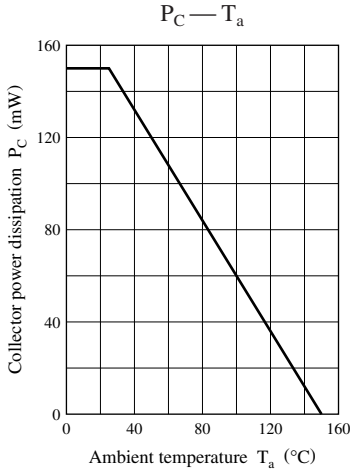
2. *1: Pulse measurement

*2: Rank classification

| Rank | R | S | T |
|----------|------------|------------|------------|
| h_{FE} | 200 to 350 | 300 to 500 | 400 to 800 |

*3: R_{on} Measurement circuit





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